

# Zi-Hui Zhang

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

139  
papers

1,789  
citations

24  
h-index

35  
g-index

148  
ext. papers

2,236  
ext. citations

3.9  
avg, IF

4.84  
L-index

#	Paper	IF	Citations
139	Simulation study for GaN-based hybrid trench MOS barrier Schottky diode with an embedded p-type NiO termination: increased forward current density and enhanced breakdown voltage. <i>Japanese Journal of Applied Physics</i> , <b>2022</b> , 61, 014002	1.4	0
138	Enhanced performance of an AlGaIn-based deep ultraviolet light-emitting diode using a p-GaN/SiO <sub>2</sub> /ITO tunnel junction.. <i>Optics Letters</i> , <b>2022</b> , 47, 798-801	3	0
137	Highly efficient and stable Eu <sup>3+</sup> -doped two-dimensional perovskites. <i>Journal of Alloys and Compounds</i> , <b>2022</b> , 902, 163841	5.7	1
136	Hybrid metal/GaN/GaN ultraviolet detector for obtaining low dark current and high responsivity.. <i>Optics Letters</i> , <b>2022</b> , 47, 1561-1564	3	0
135	3-D Simulation Study of a Normally-OFF GaN Lateral Multi-Channel JFET With Optimized Electrical Field Transfer Terminal Structure. <i>IEEE Transactions on Electron Devices</i> , <b>2022</b> , 69, 1918-1923	2.9	
134	A Buried High k Insulator for Suppressing the Surface Recombination for GaN-Based Micro-Light-Emitting Diodes. <i>IEEE Transactions on Electron Devices</i> , <b>2022</b> , 1-4	2.9	0
133	Improving the performance for flip-chip AlGaIn-based deep ultraviolet light-emitting diodes using surface textured Ga-face n-AlGaIn. <i>Optics Express</i> , <b>2022</b> , 30, 17781	3.3	
132	On the impact of a metal-insulator-semiconductor structured n-electrode for AlGaIn-based DUV LEDs.. <i>Applied Optics</i> , <b>2021</b> , 60, 11222-11226	1.7	0
131	Numerical investigations into polarization-induced self-powered GaN-based MSM photodetectors.. <i>Applied Optics</i> , <b>2021</b> , 60, 10975-10983	1.7	2
130	Eco-Friendly and Efficient Luminescent Solar Concentrators Based on a Copper(I)-Halide Composite. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 56348-56357	9.5	4
129	Three-dimensional metal-semiconductor-metal bipolar ultraviolet phototransistor based on GaN p-i-n epilayer. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 161105	3.4	4
128	Perovskite energy funnels for efficient white emission. <i>Journal of Colloid and Interface Science</i> , <b>2021</b> , 608, 1202-1211	9.3	2
127	Strain-Reduced Micro-LEDs Grown Directly Using Partitioned Growth. <i>Frontiers in Chemistry</i> , <b>2021</b> , 9, 639023	5	0
126	Direct demonstration of carrier distribution and recombination within step-bunched UV-LEDs. <i>Photonics Research</i> , <b>2021</b> , 9, 764	6	2
125	Polarization assisted self-powered GaN-based UV photodetector with high responsivity. <i>Photonics Research</i> , <b>2021</b> , 9, 734	6	9
124	Advances of beveled mesas for GaN-based trench Schottky barrier diodes. <i>AIP Advances</i> , <b>2021</b> , 11, 0453165	1.5	1
123	Step-type quantum wells with slightly varied InN composition for GaN-based yellow micro light-emitting diodes. <i>Applied Optics</i> , <b>2021</b> , 60, 3006-3012	1.7	0

122	Reducing the polarization mismatch between the last quantum barrier and p-EBL to enhance the carrier injection for AlGaIn-based DUV LEDs. <i>Optical Materials Express</i> , <b>2021</b> , 11, 1713	2.6	2
121	High-Performance Triangular Miniaturized-LEDs for High Current and Power Density Applications. <i>ACS Photonics</i> , <b>2021</b> , 8, 2304-2310	6.3	1
120	Tuning the Plasmonic Resonance Peak for Al Nanorods on AlGaIn Layer to Deep Ultraviolet Band. <i>IEEE Photonics Journal</i> , <b>2021</b> , 1-1	1.8	
119	Enhanced photodetection performance of Schottky Pt/SnS <sub>2</sub> /Al and Au/SnS <sub>2</sub> /Al photodetectors. <i>Journal of Materials Chemistry C</i> , <b>2021</b> , 9, 10472-10477	7.1	1
118	Aluminum doping effects on photoresponse characteristics of hydrothermal tin disulfide nanosheets. <i>CrystEngComm</i> , <b>2021</b> , 23, 4694-4699	3.3	2
117	Lead-free, stable orange-red-emitting hybrid copper based organic-inorganic compounds. <i>Dalton Transactions</i> , <b>2021</b> , 50, 2766-2773	4.3	7
116	A review on the low external quantum efficiency and the remedies for GaN-based micro-LEDs. <i>Journal Physics D: Applied Physics</i> , <b>2021</b> , 54, 153002	3	12
115	BAIN for III-nitride UV light-emitting diodes: undoped electron blocking layer. <i>Journal Physics D: Applied Physics</i> , <b>2021</b> , 54, 175104	3	4
114	Different scattering effect of nano-patterned sapphire substrate for TM- and TE-polarized light emitted from AlGaIn-based deep ultraviolet light-emitting diodes. <i>Optical Materials Express</i> , <b>2021</b> , 11, 729	2.6	9
113	Efficient and Stable Blue Perovskite Light-Emitting Devices Based on Inorganic CsPbBr <sub>3</sub> Spaced Low-Dimensional CsPbBr <sub>3</sub> through Synergistic Control of Amino Alcohols and Polymer Additives. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 33199-33208	9.5	3
112	Enhanced Photodetection Performance of Photodetectors Based on Indium-Doped Tin Disulfide Few Layers. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 35889-35896	9.5	4
111	Is a thin p-GaN layer possible for making high-efficiency AlGaIn-based deep-ultraviolet light-emitting diodes?. <i>Optics Express</i> , <b>2021</b> , 29, 29651-29660	3.3	1
110	Sheet Charge Engineering Towards an Efficient Hole Injection in 290 nm Deep Ultraviolet Light-Emitting Diodes. <i>IEEE Photonics Journal</i> , <b>2021</b> , 13, 1-8	1.8	1
109	Stable and highly efficient blue-emitting CsPbBr <sub>3</sub> perovskite nanomaterials via kinetic-controlled growth. <i>Chemical Engineering Journal</i> , <b>2021</b> , 419, 129612	14.7	5
108	Multiple-quantum-well-induced unipolar carrier transport multiplication in AlGaIn solar-blind ultraviolet photodiode. <i>Photonics Research</i> , <b>2021</b> , 9, 1907	6	3
107	Artificially formed resistive ITO/p-GaN junction to suppress the current spreading and decrease the surface recombination for GaN-based micro-light emitting diodes. <i>Optics Express</i> , <b>2021</b> , 29, 31201-31211	3.3	5
106	Enhancing the light extraction efficiency for AlGaIn-based DUV LEDs with a laterally over-etched p-GaN layer at the top of truncated cones. <i>Optics Express</i> , <b>2021</b> , 29, 30532-30542	3.3	4
105	Polarization Self-Screened Multiple Quantum Wells for Deep Ultraviolet Light-Emitting Diodes to Enhance the Optical Power. <i>IEEE Photonics Journal</i> , <b>2021</b> , 1-1	1.8	2

104	Promoted Hole Transport Capability by Improving Lateral Current Spreading for High-Efficiency Quantum Dot Light-Emitting Diodes. <i>Advanced Science</i> , <b>2020</b> , 7, 2001760	13.6	17
103	Doping-Induced Energy Barriers to Improve the Current Spreading Effect for AlGaIn-Based Ultraviolet-B Light-Emitting Diodes. <i>IEEE Electron Device Letters</i> , <b>2020</b> , 1-1	4.4	9
102	Effectively Confining the Lateral Current Within the Aperture for GaN Based VCSELs by Using a Reverse Biased NP Junction. <i>IEEE Journal of Quantum Electronics</i> , <b>2020</b> , 56, 1-7	2	1
101	Enhancing the lateral current injection by modulating the doping type in the p-type hole injection layer for InGaIn/GaN vertical cavity surface emitting lasers. <i>Optics Express</i> , <b>2020</b> , 28, 18035-18048	3.3	2
100	Metal-insulator-semiconductor structure for deep-ultraviolet light-emitting diodes to increase the electron injection in the cathode region. <i>Superlattices and Microstructures</i> , <b>2020</b> , 140, 106467	2.8	3
99	Design Strategies for Mesa-Type GaN-Based Schottky Barrier Diodes for Obtaining High Breakdown Voltage and Low Leakage Current. <i>IEEE Transactions on Electron Devices</i> , <b>2020</b> , 67, 1931-1938	2.9	6
98	Improving hole injection from p-EBL down to the end of active region by simply playing with polarization effect for AlGaIn based DUV light-emitting diodes. <i>AIP Advances</i> , <b>2020</b> , 10, 065032	1.5	9
97	On the Impact of Electron Leakage on the Efficiency Droop for AlGaIn Based Deep Ultraviolet Light Emitting Diodes. <i>IEEE Photonics Journal</i> , <b>2020</b> , 12, 1-7	1.8	6
96	On the origin for the hole confinement into apertures for GaN-based VCSELs with buried dielectric insulators. <i>Optics Express</i> , <b>2020</b> , 28, 8668-8679	3.3	6
95	Integrating remote reflector and air cavity into inclined sidewalls to enhance the light extraction efficiency for AlGaIn-based DUV LEDs. <i>Optics Express</i> , <b>2020</b> , 28, 17035-17046	3.3	8
94	128-pixel arrays of 4H-SiC UV APD with dual-frequency PECVD SiN passivation. <i>Optics Express</i> , <b>2020</b> , 28, 29245-29252	3.3	2
93	Polarization-enhanced AlGaIn solar-blind ultraviolet detectors. <i>Photonics Research</i> , <b>2020</b> , 8, 1243	6	17
92	Demonstration of ohmic contact using $\text{MoO}_x/\text{Al}$ on p-GaN and the proposal of a reflective electrode for AlGaIn-based DUV-LEDs. <i>Optics Letters</i> , <b>2020</b> , 45, 2427-2430	3	2
91	Enhanced Photoresponse of Indium-Doped Tin Disulfide Nanosheets. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 2607-2614	9.5	7
90	Understanding omni-directional reflectors and nominating more dielectric materials for deep ultraviolet light-emitting diodes with inclined sidewalls. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 093106	2.5	6
89	Advantage of SiO <sub>2</sub> Intermediate Layer on the Electron Injection for Ti/n-Al <sub>0.60</sub> Ga <sub>0.40</sub> N Structure. <i>IEEE Transactions on Electron Devices</i> , <b>2020</b> , 67, 3548-3552	2.9	1
88	Improving the Current-Spreading Effect for GaN-Based Quasi-Vertical PIN Diode by Using an Embedded PN Junction. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2020</b> , 217, 2000146	1.6	2
87	Improved carrier confinement and stimulated recombination rate in GaN-based vertical-cavity surface-emitting lasers with buried p-AlGaIn inversion layer. <i>Superlattices and Microstructures</i> , <b>2020</b> , 146, 106654	2.8	

86	Alternative Strategy to Reduce Surface Recombination for InGaN/GaN Micro-light-Emitting Diodes-Thinning the Quantum Barriers to Manage the Current Spreading. <i>Nanoscale Research Letters</i> , <b>2020</b> , 15, 160	5	7
85	Boosting the Efficiency and Stability of Perovskite Light-Emitting Devices by a 3-Amino-1-propanol-Tailored PEDOT:PSS Hole Transport Layer. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 43331-43338	9.5	8
84	Highly efficient Mn-doped CsPb(Cl/Br) quantum dots for white light-emitting diodes. <i>Nanotechnology</i> , <b>2020</b> , 31, 065603	3.4	8
83	Enhanced Optical Performance of AlGaIn-Based Deep Ultraviolet Light-Emitting Diodes by Electrode Patterns Design. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 1925-1928	4.4	9
82	Effects of Meshed p-type Contact Structure on the Light Extraction Effect for Deep Ultraviolet Flip-Chip Light-Emitting Diodes. <i>Nanoscale Research Letters</i> , <b>2019</b> , 14, 149	5	10
81	8x8 4H-SiC Ultraviolet Avalanche Photodiode Arrays With High Uniformity. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 1591-1594	4.4	6
80	High color rendering index and stable white light emitting diodes fabricated from lead bromide perovskites. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 153103	3.4	8
79	Influence of an Insulator Layer on the Charge Transport in a Metal/Insulator/n-AlGaIn Structure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1800810	1.6	5
78	One Stone, Two Birds: High-Efficiency Blue-Emitting Perovskite Nanocrystals for LED and Security Ink Applications. <i>Chemistry of Materials</i> , <b>2019</b> , 31, 5116-5123	9.6	43
77	Deep Ultraviolet LEDs. <i>SpringerBriefs in Applied Sciences and Technology</i> , <b>2019</b> ,	0.4	1
76	Improving the Current Spreading by Locally Modulating the Doping Type in the n-AlGaIn Layer for AlGaIn-Based Deep Ultraviolet Light-Emitting Diodes. <i>Nanoscale Research Letters</i> , <b>2019</b> , 14, 268	5	3
75	Modulating the Layer Resistivity by Band-Engineering to Improve the Current Spreading for DUUV LEDs. <i>IEEE Photonics Technology Letters</i> , <b>2019</b> , 31, 1201-1204	2.2	7
74	Orange to Red, Emission-Tunable Mn-Doped Two-Dimensional Perovskites with High Luminescence and Stability. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 34109-34116	9.5	45
73	Polarization Engineering to Manipulate the Breakdown Voltage for GaN-Based PIN Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1900210	1.6	2
72	Unambiguously Enhanced Ultraviolet Luminescence of AlGaIn Wavy Quantum Well Structures Grown on Large Misoriented Sapphire Substrate. <i>Advanced Functional Materials</i> , <b>2019</b> , 29, 1905445	15.6	85
71	On the origin of enhanced hole injection for AlGaIn-based deep ultraviolet light-emitting diodes with AlN insertion layer in p-electron blocking layer. <i>Optics Express</i> , <b>2019</b> , 27, A620-A628	3.3	39
70	Impact of the surface recombination on InGaIn/GaN-based blue micro-light emitting diodes. <i>Optics Express</i> , <b>2019</b> , 27, A643-A653	3.3	58
69	High-performance nanoporous-GaN metal-insulator-semiconductor ultraviolet photodetectors with a thermal oxidized eGaO layer. <i>Optics Letters</i> , <b>2019</b> , 44, 2197-2200	3	14

68	Three-dimensional band diagram in lateral polarity junction III-nitride heterostructures. <i>Optica</i> , <b>2019</b> , 6, 1058	8.6	10
67	Increasing the hole energy by grading the alloy composition of the p-type electron blocking layer for very high-performance deep ultraviolet light-emitting diodes. <i>Photonics Research</i> , <b>2019</b> , 7, B1	6	32
66	Screen the Polarization Induced Electric Field Within the MQWs for DUV LEDs. <i>SpringerBriefs in Applied Sciences and Technology</i> , <b>2019</b> , 43-57	0.4	0
65	Improve the Hole Injection to Enhance the IQE for DUV LEDs. <i>SpringerBriefs in Applied Sciences and Technology</i> , <b>2019</b> , 11-31	0.4	
64	White light-emitting diodes based on carbon dots and Mn-doped CsPbMnCl nanocrystals. <i>Nanotechnology</i> , <b>2019</b> , 30, 245201	3.4	18
63	Enhance the Electron Injection Efficiency for DUV LEDs. <i>SpringerBriefs in Applied Sciences and Technology</i> , <b>2019</b> , 33-42	0.4	
62	The Light Extraction Efficiency for DUV LEDs. <i>SpringerBriefs in Applied Sciences and Technology</i> , <b>2019</b> , 61-65	0.4	
61	Optimization Strategy of 4H-SiC Separated Absorption Charge and Multiplication Avalanche Photodiode Structure for High Ultraviolet Detection Efficiency. <i>Nanoscale Research Letters</i> , <b>2019</b> , 14, 396	5	5
60	Interplay between various active regions and the interband transition for AlGaN-based deep-ultraviolet light-emitting diodes to enable a reduced TM-polarized emission. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 245702	2.5	5
59	The Effect of Sapphire Substrates on Omni-Directional Reflector Design for Flip-Chip Near-Ultraviolet Light-Emitting Diodes. <i>IEEE Photonics Journal</i> , <b>2019</b> , 11, 1-9	1.8	6
58	On the Carrier Transport for InGaN/GaN Core-Shell Nanorod Green Light-Emitting Diodes. <i>IEEE Nanotechnology Magazine</i> , <b>2019</b> , 18, 176-182	2.6	5
57	The morphology evolution of selective area wet etched commercial patterned sapphire substrates. <i>Journal of Micromechanics and Microengineering</i> , <b>2019</b> , 29, 035012	2	7
56	On the Light Extraction Efficiency for III-Nitride-Based Light-Emitting Diodes. <i>Solid State Lighting Technology and Application Series</i> , <b>2019</b> , 311-335	0.7	
55	Progress in External Quantum Efficiency for III-Nitride Based Deep Ultraviolet Light-Emitting Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1800815	1.6	24
54	Atmospheric Aerosol Multiband Synthesis Imaging Spectrometer. <i>Applied Spectroscopy</i> , <b>2019</b> , 73, 221-228	3.1	1
53	High-efficiency all-inorganic full-colour quantum dot light-emitting diodes. <i>Nano Energy</i> , <b>2018</b> , 46, 229-233	3.1	33
52	Temperature-Dependent Efficiency Droop in GaN-Based Blue LEDs. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 528-531	4.4	16
51	Enhanced the Optical Power of AlGaN-Based Deep Ultraviolet Light-Emitting Diode by Optimizing Mesa Sidewall Angle. <i>IEEE Photonics Journal</i> , <b>2018</b> , 10, 1-7	1.8	18

50	Establishment of the relationship between the electron energy and the electron injection for AlGa <sub>N</sub> based ultraviolet light-emitting diodes. <i>Optics Express</i> , <b>2018</b> , 26, 17977-17987	3.3	19
49	On the polarization effect of the p-EBL/p-AlGa <sub>N</sub> /p-GaN structure for AlGa <sub>N</sub> -based deep-ultraviolet light-emitting diodes. <i>Superlattices and Microstructures</i> , <b>2018</b> , 122, 280-285	2.8	7
48	Enhancing Both TM- and TE-Polarized Light Extraction Efficiency of AlGa <sub>N</sub> -Based Deep Ultraviolet Light-Emitting Diode via Air Cavity Extractor With Vertical Sidewall. <i>IEEE Photonics Journal</i> , <b>2018</b> , 10, 1-9	1.8	11
47	Manipulation of Si Doping Concentration for Modification of the Electric Field and Carrier Injection for AlGa <sub>N</sub> -Based Deep-Ultraviolet Light-Emitting Diodes. <i>Crystals</i> , <b>2018</b> , 8, 258	2.3	4
46	Nearly Efficiency-Droop-Free AlGa <sub>N</sub> -Based Ultraviolet Light-Emitting Diodes with a Specifically Designed Superlattice p-Type Electron Blocking Layer for High Mg Doping Efficiency. <i>Nanoscale Research Letters</i> , <b>2018</b> , 13, 122	5	32
45	Fabrication and Growth Mechanism of Uniform Suspended Perovskite Thin Films. <i>Crystal Growth and Design</i> , <b>2018</b> , 18, 5770-5779	3.5	2
44	Very high external quantum efficiency and wall-plug efficiency 527 nm InGa <sub>N</sub> green LEDs by MOCVD. <i>Optics Express</i> , <b>2018</b> , 26, 33108-33115	3.3	21
43	Investigations on AlGa <sub>N</sub> -Based Deep-Ultraviolet Light-Emitting Diodes With Si-Doped Quantum Barriers of Different Doping Concentrations. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2018</b> , 12, 1700346	2.5	25
42	On the Al <sub>x</sub> Ga <sub>1-x</sub> N/Al <sub>y</sub> Ga <sub>1-y</sub> N/Al <sub>x</sub> Ga <sub>1-x</sub> N (x>y) p-electron blocking layer to improve the hole injection for AlGa <sub>N</sub> based deep ultraviolet light-emitting diodes. <i>Superlattices and Microstructures</i> , <b>2018</b> , 113, 472-477	2.8	18
41	On the p-AlGa <sub>N</sub> /n-AlGa <sub>N</sub> /p-AlGa <sub>N</sub> Current Spreading Layer for AlGa <sub>N</sub> -based Deep Ultraviolet Light-Emitting Diodes. <i>Nanoscale Research Letters</i> , <b>2018</b> , 13, 355	5	15
40	Improved the AlGa <sub>N</sub> -Based Ultraviolet LEDs Performance With Super-Lattice Structure Last Barrier. <i>IEEE Photonics Journal</i> , <b>2018</b> , 10, 1-7	1.8	7
39	Investigation of p-type depletion doping for InGa <sub>N</sub> /Ga <sub>N</sub> -based light-emitting diodes. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 033506	3.4	15
38	Hole Transport Manipulation To Improve the Hole Injection for Deep Ultraviolet Light-Emitting Diodes. <i>ACS Photonics</i> , <b>2017</b> , 4, 1846-1850	6.3	72
37	A dielectric-constant-controlled tunnel junction for III-nitride light-emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1600937	1.6	12
36	Numerical Investigations on the n <sup>+</sup> -Ga <sub>N</sub> /AlGa <sub>N</sub> /p <sup>+</sup> -Ga <sub>N</sub> Tunnel Junction for III-Nitride UV Light-Emitting Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1700624	1.6	5
35	Formation of "Steady Size" State for Accurate Size Control of CdSe and CdS Quantum Dots. <i>Journal of Physical Chemistry Letters</i> , <b>2017</b> , 8, 3576-3580	6.4	10
34	Effects of Inclined Sidewall Structure With Bottom Metal Air Cavity on the Light Extraction Efficiency for AlGa <sub>N</sub> -Based Deep Ultraviolet Light-Emitting Diodes. <i>IEEE Photonics Journal</i> , <b>2017</b> , 9, 1-9	1.8	8
33	On the electric-field reservoir for III-nitride based deep ultraviolet light-emitting diodes. <i>Optics Express</i> , <b>2017</b> , 25, 16550-16559	3.3	40

32	UVA light-emitting diode grown on Si substrate with enhanced electron and hole injections. <i>Optics Letters</i> , <b>2017</b> , 42, 4533-4536	3	23
31	Synthesis of Quantum Dot-ZnS Nanosheet Inorganic Assembly with Low Thermal Fluorescent Quenching for LED Application. <i>Materials</i> , <b>2017</b> , 10,	3.5	2
30	On the Hole Injection for III-Nitride Based Deep Ultraviolet Light-Emitting Diodes. <i>Materials</i> , <b>2017</b> , 10,	3.5	23
29	On the internal quantum efficiency for InGaN/GaN light-emitting diodes grown on insulating substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 3078-3102	1.6	14
28	Decoupling contact and mirror: an effective way to improve the reflector for flip-chip InGaN/GaN-based light-emitting diodes. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 265106	3	6
27	A charge inverter for III-nitride light-emitting diodes. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 133502	3.4	9
26	On the hole accelerator for III-nitride light-emitting diodes. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 151105	3.4	17
25	Interface and photoluminescence characteristics of graphene-(GaN/InGaN)n multiple quantum wells hybrid structure. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 143105	2.5	2
24	On the Importance of the Polarity for GaN/InGaN Last Quantum Barriers in III-Nitride-Based Light-Emitting Diodes. <i>IEEE Photonics Journal</i> , <b>2016</b> , 8, 1-7	1.8	2
23	Nonradiative recombination--critical in choosing quantum well number for InGaN/GaN light-emitting diodes. <i>Optics Express</i> , <b>2015</b> , 23, A34-42	3.3	19
22	Current Crowding Phenomenon: Theoretical and Direct Correlation With the Efficiency Droop of Light Emitting Diodes by a Modified ABC Model. <i>IEEE Journal of Quantum Electronics</i> , <b>2015</b> , 51, 1-9	2	8
21	A hole modulator for InGaN/GaN light-emitting diodes. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 063501	3.4	18
20	Graphene-based transparent conductive electrodes for GaN-based light emitting diodes: Challenges and countermeasures. <i>Nano Energy</i> , <b>2015</b> , 12, 419-436	17.1	73
19	Simultaneous enhancement of electron overflow reduction and hole injection promotion by tailoring the last quantum barrier in InGaN/GaN light-emitting diodes. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 161113	3.4	13
18	Advantages of the Blue InGaN/GaN Light-Emitting Diodes with an AlGaIn/GaN/AlGaIn Quantum Well Structured Electron Blocking Layer. <i>ACS Photonics</i> , <b>2014</b> , 1, 377-381	6.3	28
17	On the origin of the electron blocking effect by an n-type AlGaIn electron blocking layer. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 073511	3.4	27
16	Low thermal-mass LEDs: size effect and limits. <i>Optics Express</i> , <b>2014</b> , 22, 32200-7	3.3	10
15	On the effect of N-GaN/P-GaN/N-GaN/P-GaN/N-GaN built-in junctions in the n-GaN layer for InGaN/GaN light-emitting diodes. <i>Optics Express</i> , <b>2014</b> , 22, 809-16	3.3	6



14	On the mechanisms of InGaN electron cooler in InGaN/GaN light-emitting diodes. <i>Optics Express</i> , <b>2014</b> , 22 Suppl 3, A779-89	3-3	26
13	Improving hole injection efficiency by manipulating the hole transport mechanism through p-type electron blocking layer engineering. <i>Optics Letters</i> , <b>2014</b> , 39, 2483-6	3	33
12	Polarization self-screening in [0001] oriented InGaN/GaN light-emitting diodes for improving the electron injection efficiency. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 251108	3-4	25
11	Self-screening of the quantum confined Stark effect by the polarization induced bulk charges in the quantum barriers. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 243501	3-4	42
10	A hole accelerator for InGaN/GaN light-emitting diodes. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 153503	3-4	29
9	Comparative study of field-dependent carrier dynamics and emission kinetics of InGaN/GaN light-emitting diodes grown on (112̄) semipolar versus (0001) polar planes. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 143506	3-4	26
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1	Enhanced hole transport in InGaN/GaN multiple quantum well light-emitting diodes with a p-type doped quantum barrier. <i>Optics Letters</i> , <b>2013</b> , 38, 202-4	3	29